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(54) Title: DIELECTRIC FILMS FROM ORGANOHYDRIDOSILOXANE RESINS

(57) Abstract

A method of making a dielectric film on a substrate from a composition containing an organohydridosiloxane resin is presented. The organohydridosiloxane resins have a cage conformation. The process of making a dielectric film includes forming a solution of a solvent and the organohydridosiloxane resin, dispensing the solution on a substrate, spinning the substrate, baking the substrate to remove the solvent, and curing the substrate to form the dielectric film. Dielectric films of the present invention exhibit dielectric constants of approximately 3.0 or lower.